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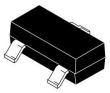
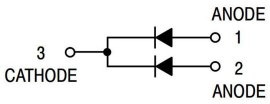
MMBD2837LT1G, MMBD2838LT1G, Monolithic Dual Switching Diodes



SOT−23 (TO−236AB)
CASE 318
STYLE 9



Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	75	Vdc
D.C. Reverse Voltage MMBD2837LT1G, MMBD2838LT1G	V_R	 30 50	Vdc
Peak Forward Current	I_{FM}	450 300	mAdc
Average Rectified Current	I_O	150 100	mAdc

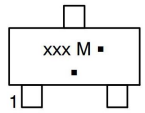
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	 556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	 417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



xxx = Specific Device Code
A5 = MMBD2837LT1G, SMMBD2837LT1G
MA6 = MMBD2838LT1G
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

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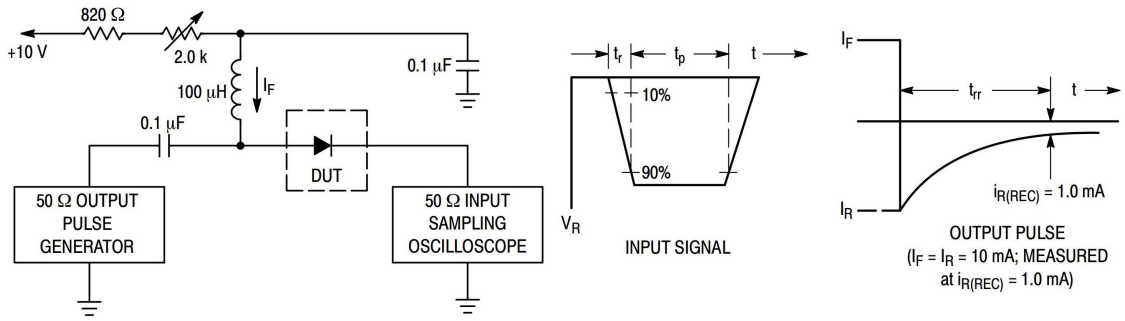
ELECTRICAL CHARACTERISTICS (EACH DIODE) (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc) MMBD2837LT1G, MMBD2838LT1G	$V_{(BR)}$	35 75	– –	Vdc
Reverse Voltage Leakage Current (Note 3.) (V_R = 30 Vdc) MMBD2837LT1G, (V_R = 50 Vdc) MMBD2838LT1G	I_R	– –	0.1 0.1	μAdc
Diode Capacitance (V_R = 0 V, f = 1.0 MHz)	C_T	–	4.0	pF
Forward Voltage (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 100 mAdc)	V_F	– – –	1.0 1.0 1.2	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc) (Figure 1)	t_{rr}	–	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while the second diode is unbiased.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
Notes: 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
Notes: 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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CURVES APPLICABLE TO EACH CATHODE

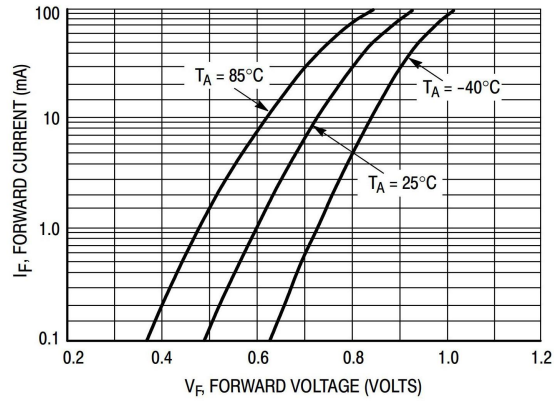

Figure 2. Forward Voltage

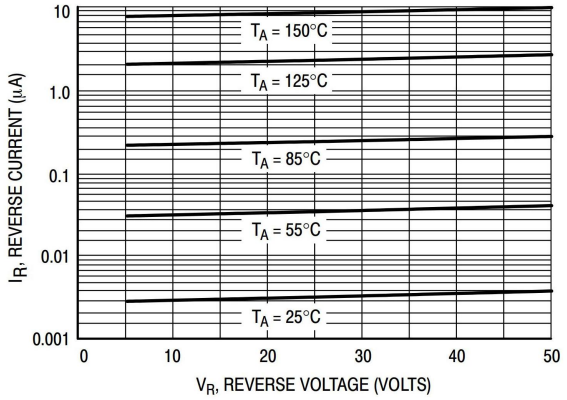

Figure 3. Leakage Current

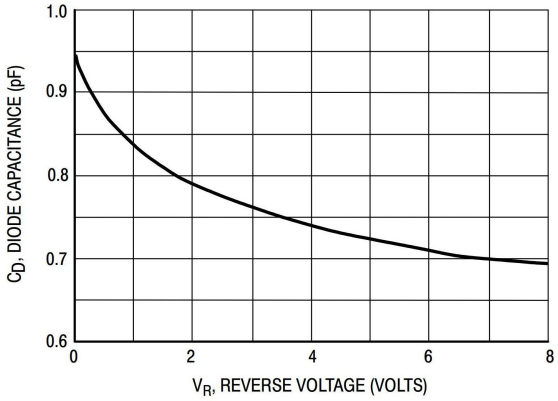

Figure 4. Capacitance

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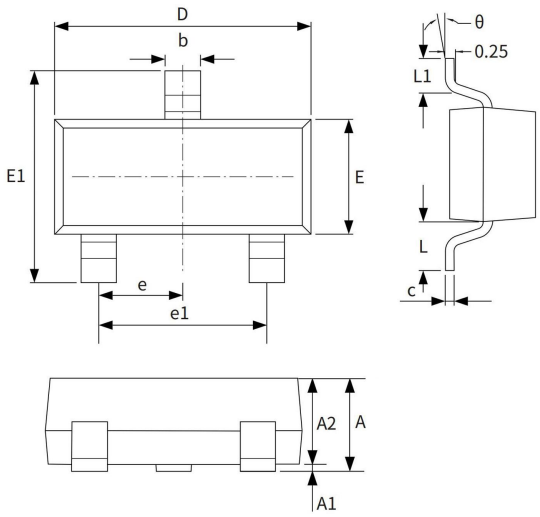
Ordering Information

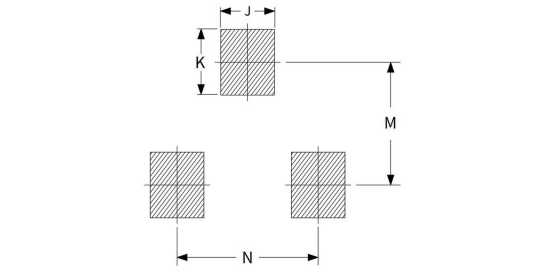
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077